

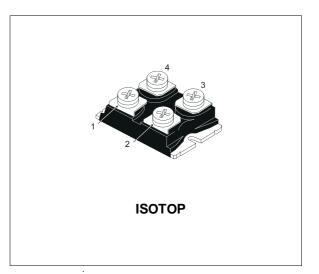
# **BUF460AV**

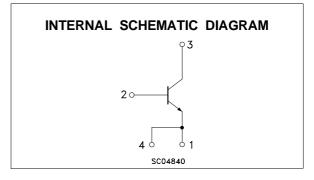
# NPN TRANSISTOR POWER MODULE

- EASY TO DRIVE TECHNOLOGY (ETD)
- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW Rth JUNCTION CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- LOW INTERNAL PARASITIC INDUCTANCE

### **APPLICATIONS:**

- MOTOR CONTROL
- SMPS & UPS
- WELDING EQUIPMENT





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CEV}$	Collector-Emitter Voltage (V <sub>BE</sub> = -5 V)	1000	V
V <sub>CEO(sus)</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	450	V
VEBO	Emitter-Base Voltage $(I_C = 0)$	7	V
Ic	Collector Current	80	А
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> = 10 ms)	160	A
IB	Base Current	18	A
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> = 10 ms)	27	A
Ptot	Total Dissipation at T <sub>c</sub> = 25 °C	270	W
Visol	Insulation Withstand Voltage (RMS) from All Four Terminals to External Heatsink	2500	
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
Tj	Max Operation Junction Temperature	150	°C

# THERMAL DATA

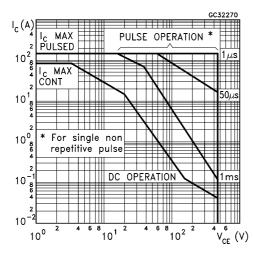
R <sub>thj-case</sub>	Thermal Resistance	Junction-case	Max	0.41	°C/W	
R <sub>thc-h</sub>	Thermal Resistance	Case-heatsink Wi	th Conductive			
	Grease Applied		Max	0.05	°C/W	

# **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

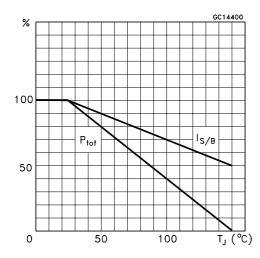
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CER</sub>	Collector Cut-off Current ( $R_{BE} = 5 \Omega$ )				0.2 2	mA mA
I <sub>CEV</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ $T_j = 100 \ ^{\circ}C$			0.2 2	mA mA
Іево	Emitter Cut-off Current $(I_C = 0)$	Veb = 5 V			1	mA
$V_{CEO(sus)}^{\star}$	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	$I_{C} = 0.2 \text{ A} \qquad L = 25 \text{ mH}$ $V_{clamp} = 450 \text{ V}$	450			V
h <sub>FE</sub> *	DC Current Gain	$I_{C} = 60 \text{ A}$ $V_{CE} = 5 \text{ V}$		15		
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	$I_{C} = 30 \text{ A}$ $I_{B} = 3 \text{ A}$ $I_{C} = 30 \text{ A}$ $I_{B} = 3 \text{ A}$ $T_{j} = 100 ^{\circ}\text{C}$		0.35	2	V V
				0.5	2	V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage			1.1	1.5	V V
di <sub>C</sub> /dt	Rate of Rise of On-state Collector		150			A/µs
V <sub>CE</sub> (3 μs)•	Collector-Emitter Dynamic Voltage			4	6	V
V <sub>CE</sub> (5 μs)•	Collector-Emitter Dynamic Voltage			2	3	V
t <sub>s</sub> t <sub>f</sub> t <sub>c</sub>	Storage Time Fall Time Cross-over Time			4.5 0.1 0.3	5 0.2 5	μs μs μs
V <sub>CEW</sub>	Maximum Collector Emitter Voltage Without Snubber		400			V

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

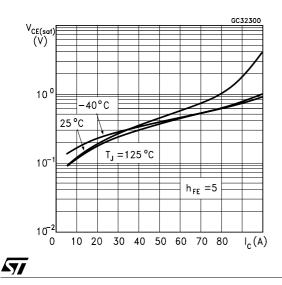
#### Safe Operating Area



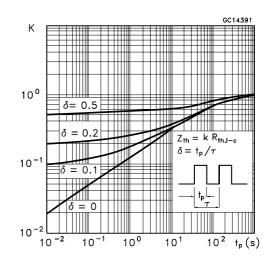
#### **Derating Curve**



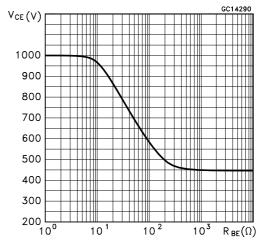
### Collector-Emitter Saturation Voltage



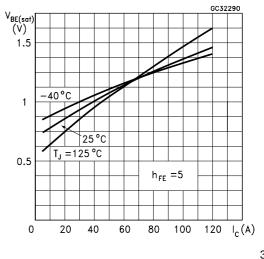
#### **Thermal Impedance**



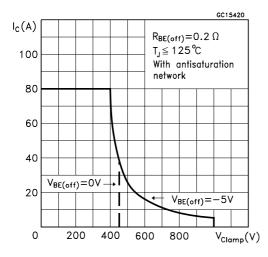
#### Collector-Emitter Voltage Versus Base-Emitter Resistance



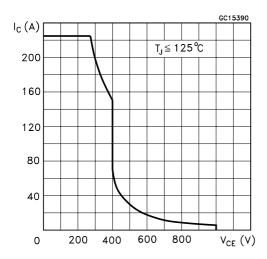




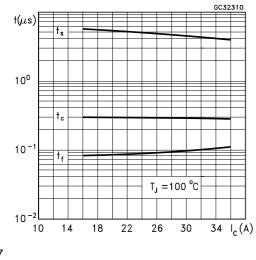
# **Reverse Biased SOA**



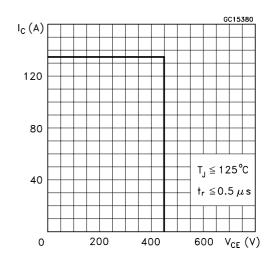
#### **Reverse Biased SOA**



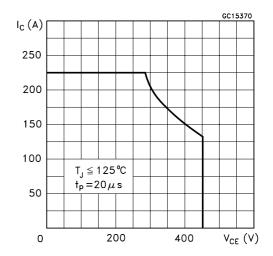
### Switching Time Inductive Load

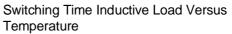


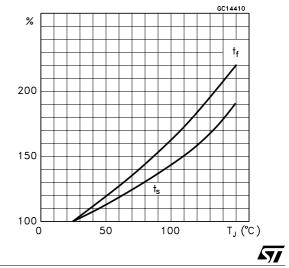
Forward Biased SOA



# Forward Biased SOA

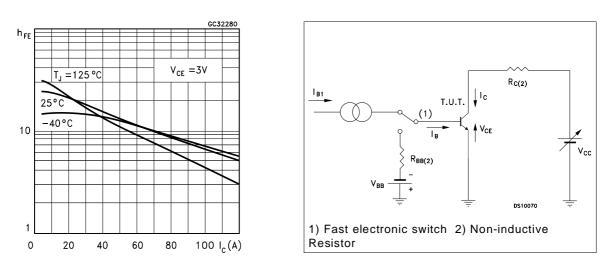




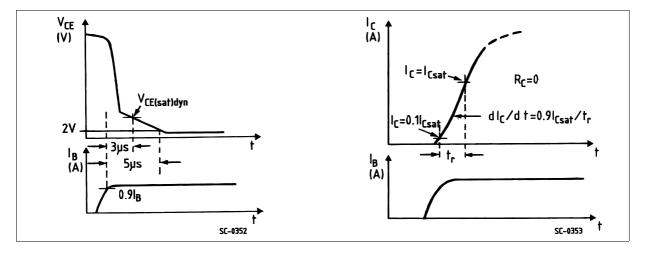


# DC Current Gain

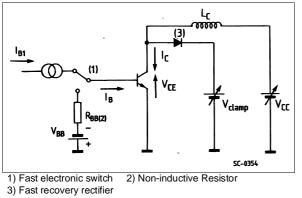
Turn-off Switching Test Circuit



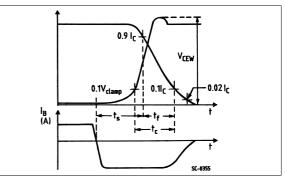
Turn-on Switching Waveforms.



Turn-off Switching Test Circuit



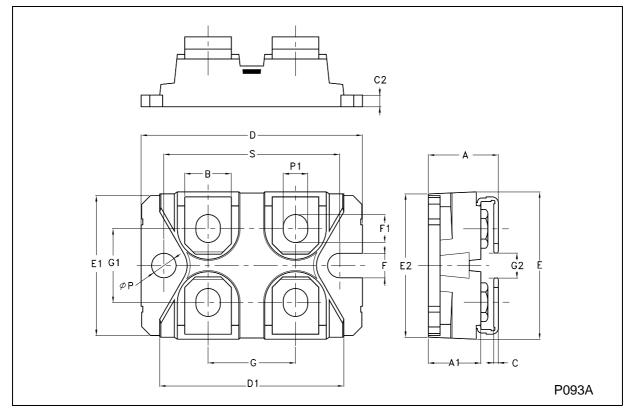
Turn-off Switching Waveforms.



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DIM.		mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	11.8		12.2	0.465		0.480	
A1	8.9		9.1	0.350		0.358	
В	7.8		8.2	0.307		0.322	
С	0.75		0.85	0.029		0.033	
C2	1.95		2.05	0.076		0.080	
D	37.8		38.2	1.488		1.503	
D1	31.5		31.7	1.240		1.248	
E	25.15		25.5	0.990		1.003	
E1	23.85		24.15	0.938		0.950	
E2		24.8			0.976		
G	14.9		15.1	0.586		0.594	
G1	12.6		12.8	0.496		0.503	
G2	3.5		4.3	0.137		1.169	
F	4.1		4.3	0.161		0.169	
F1	4.6		5	0.181		0.196	
Р	4		4.3	0.157		0.169	
P1	4		4.4	0.157		0.173	





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